

NTE3028 Infrared Emitting Diode PN Gallium Arsenide

Description:

The NTE3028 is designed for applications requiring high power output, low drive power, and very fast response time. This device is used in industrial processing and control, light modulators, shaft or position encoders, punched card readers, optical switching, and logic circuits. It is spectrally matched for use with silicon detectors.

Features:

- High Power Output
- Infrared Emission
- Low Drive Current
- Popular TO18 Type Package for Easy Handling and Mounting

Absolute Maximum Ratings:

| Reverse Voltage, V _R | |
|---|----------------|
| Forward Current, I _F | |
| Continuous | |
| Peak (PW = 100μs, Duty Cycle = 2%) | 1A |
| Total Device Dissipation (T _A = +25°C), P _D | |
| Derate Above 25°C (Note 1) | 2.27mW/°C |
| Operating Temperature Range, T _A | –55° to +125°C |
| Storage Temperature Range, T _{stg} | 65° to +150°C |
| | |

Note 1. Printed circuit board mounting.

Electrical Characteristics: $(T_A = +25^{\circ}C \text{ unless otherwise specified})$

| Parameter | Symbol | Test Conditions | Min | Тур | Max | Unit |
|---------------------------|--------------------|------------------------|-----|------|-----|------|
| Reverse Leakage Current | I _R | $V_R = 3V$ | _ | 2 | _ | nA |
| Reverse Breakdown Voltage | V _{(BR)R} | I _R = 100μA | 6 | 20 | _ | V |
| Forward Voltage | V _F | I _F = 50mA | _ | 1.32 | 1.5 | V |
| Total Capacitance | C _T | $V_R = 0V, f = 1MHz$ | _ | 18 | _ | рF |

<u>Optical Characteristics:</u> $(T_A = +25^{\circ}C \text{ unless otherwise specified})$

| Parameter | Symbol | Test Conditions | Min | Тур | Max | Unit |
|--------------------------|----------------|--|-----|-----|-----|------------------|
| Total Output Power | Po | I _F = 60mA, Note 2 | _ | 2.5 | _ | mW |
| | | I _F = 100mA, Note 2, Note 3 | 1.0 | 4.0 | _ | mW |
| Radiant Intensity | I _O | I _F = 100mA, Note 3, Note 4 | _ | 1.5 | _ | mW/ steradian |
| Peak Emission Wavelength | λР | | _ | 940 | _ | nm |
| Spectral Line Half Width | Δλ | | _ | 40 | _ | nm |

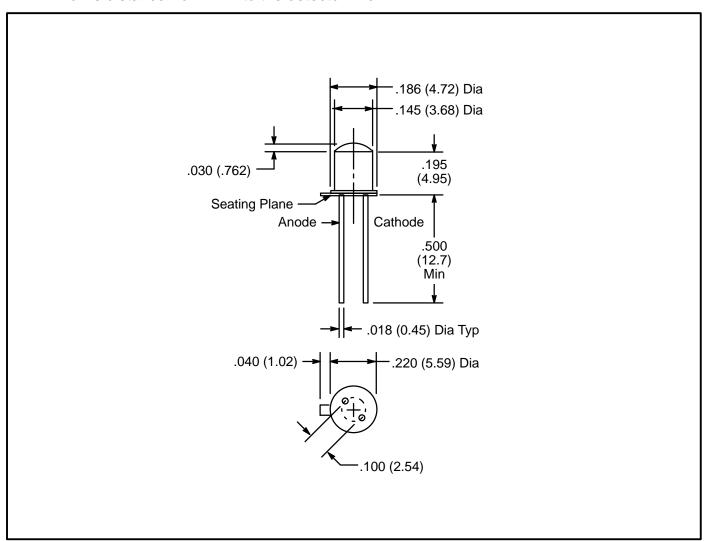
- Note 2. Power Output, P_O , is the total power radiated by th device into a solid angle of 2π steradians. It is measured by directing all radiation leaving the device, within this solid angle, onto a calibrated silicon solar cell.
- Note 3. PW = $100\mu s$, Duty Cycle = 2%.
- Note 4. Irradiance from a Light Emitting Diode (LED) can be calculated by:

$$H = \frac{I_e}{d^2}$$

where

H is irradiance in mW/cm²

I_e is radiant intensity in mW/steradian d² is distance from LED to the detector in cm



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